

Silicon PNP Power Transistor

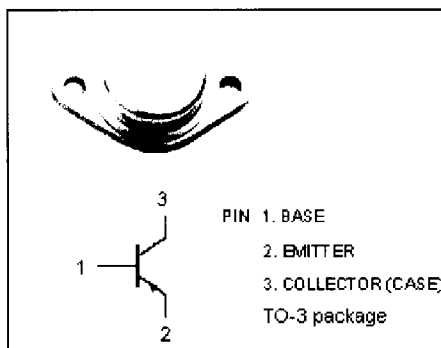
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DESCRIPTION

- High Power Dissipation-
 : $P_C = 100W(\text{Max.})@T_C=25^\circ C$
- Collector-Emitter Breakdown Voltage-
 : $V_{(BR)CEO} = -130V(\text{Min.})$

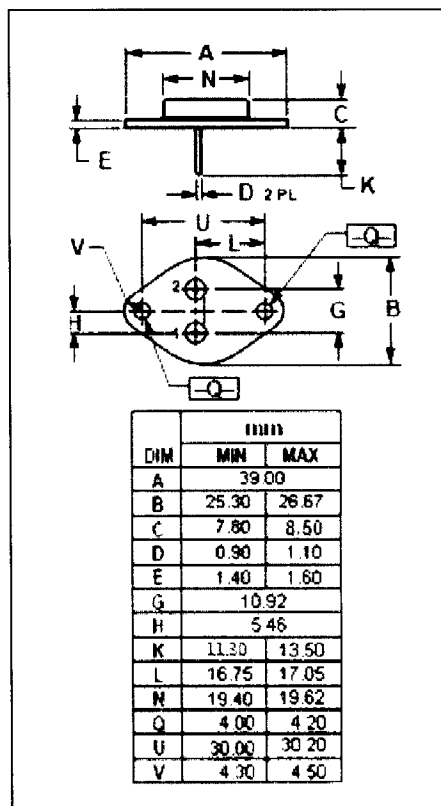
APPLICATIONS

- Designed for power and switching applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-130	V
V_{CEO}	Collector-Emitter Voltage	-130	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-7	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	100	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-65~200	$^\circ C$



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ELECTRICAL CHARACTERISTICS

$T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; I_B = 0$	-130			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.3\text{A}$			-1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -7\text{A}; I_B = -1.5\text{A}$			-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -3\text{A}; V_{CE} = -4\text{V}$			-1.6	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -130\text{V}; I_E = 0$			-0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-0.1	mA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	40			
h_{FE-2}	DC Current Gain	$I_C = -3\text{A}; V_{CE} = -4\text{V}$	20			